

**Test Report** 

No. 2151444/TY

Date: Jun 14 2007

Page 1 of 3

RICOH COMPANY LTD 13-1 HIMEMURO -CHO IKEDA-CITY OSAKA 563-8501 **JAPAN** 

The following sample was submitted and identified by the client as POWER MANAGEMENT ICS.

SGS Job No.

2358932

Style / Item No.

1. R1211Nxxxx-TX-Fx 2. R1221Nxxxx-TX-Fx 3. R1225Nxxxx-TX-Fx 4. R5210Nxxxx-TX-Fx 5. R5322Nxxxx-TX-Fx

Manufacturer

RICOH COMPANY LTD

Country of Origin

JAPAN

Sample Receiving Date

MAY 02 2007

**Testing Period** 

MAY 03 - 09 2007

Test Requested : With reference to RoHS Directive 2002/95/EC, and its amendment directives

Test Method

With reference to IEC 62321 (Ed. 1) 111/54/CDV

Procedures for the Determination of Levels of Regulated Substances in

Electrotechnical Products by Chemical Method

Determination of Lead & Cadmium by ICP/ AAS

Determination of Mercury by ICP/ CV-AAS

Determination of Hexavalent Chromium by Colorimetric Method

Determination of PBB and PBDE by GC/MS

Test Results

Please refer to next page.

Conclusion

Based on the performed tests on submitted samples, the results comply with the

RoHS Directive 2002/95/EC and its subsequent amendments.

Signed for and on behalf of SGS Hong Kong Ltd.

Wong Tak Ming, William Operations Manager

This document is issued by the Company subject to its General Conditions of Service printed overleaf or available on request and accessible at <a href="https://www.sgs.com">www.sgs.com</a>. Attention is drawn to the limitations of liability, indemnification and jurisdictional issues defined therein. Unless otherwise stated, (a) the results shown in this document referency to the sample(s) tested and (b) such sample(s) are retained for 30 days only. This document cannot be reproduced except in full, without prior approval of the Company. Any unauthorized alteration, lorgery or falsification of the content or appearance of this report is unlawful and offenders may be prosecuted to the fullest extent of the law.



# **Test Report**

No. 2151444/TY

Date : Jun 14 2007

Page 2 of 3

Test results (Unit: mg/kg):

Cadmium(Cd)	1	MDL	RoHS Limi
Lead (Pb)	ND	5	100
Mercury (Hg)	ND	5	1000
Hexavalent Chromium (CrVI)	ND ND	5	1000
by alkaline extraction	ND	5	
Polybrominated Biphenyl (PBBs)			1000
Monobromobiphenyl	< 50	50	1000
Dibromobiphenyl	ND	5	_
Tribromobiphenyl .	ND ND	5	_
Tetrabromobiphenyl	ND ND	5	-
Hexabromobiphenyl	ND	5	-
Pentabromobiphenyl	ND	5	-
Heptabromobiphenyl	ND	5	-
Octabromobiphenyl	ND	5	
Nonabromobiphenyl	ND	5	-
	ND	5	
Decabromobiphenyl	ND	5	
Polybrominated Diphenylethers (PBDEs)*	< 45	45	1000
Monobromodiphenyl ether	ND	5	1000
Dibromodiphenyl ether	ND	5	
Tribromodiphenyl ether	ND	5	
Tetrabromodiphenyl ether	ND	5	
Pentabromodiphenyl ether	ND	5	_
lexabromodiphenyl ether	ND	5	-
leptabromodiphenyl ether	ND	5	•
Octabromodiphenyl ether	ND	5	-
lonabromodiphenyl ether	ND	5	-
ecabromodiphenyl ether*	ND	5	-
um of PBDEs (Mono to Deca)	< 50	50	-

# Sample Description:

Black Ceramic (IC) w/ Silvery Metal (Foot)

#### Note:

- (1) mg/kg = ppm
- (2) ND = Not Detected
- (3) MDL = Method Detection Limit
- (4) < = Less Than
- (5) \* = sum of Mono to NonaBDE & according to 2005/717/EC DecaBDE is exempt.
- (6) -= Not Regulated
- (7) The maximum permissible limit is quoted from the document 2005/618/EC amending RoHS directive 2002/95/EC.

Remark: This report is to supersede test report no. 2146816/TY.

This document is issued by the Company subject to its General Conditions of Service printed overleaf or available on request and accessible at <a href="www.sgs.com">www.sgs.com</a>. Attention is drawn to the limitations of liability, indemnification and jurisdictional issues defined therein. Unless otherwise stated: (a) the results shown in this document refer only to the sample(s) are retained for 30 days only. This document cannot be reproduced except in full, without prior approval of the Company. Any unauthorized alteration, torgery or falsification of the content or appearance of this report is unlawful and offenders may be prosecuted to the fullest extent of the law.

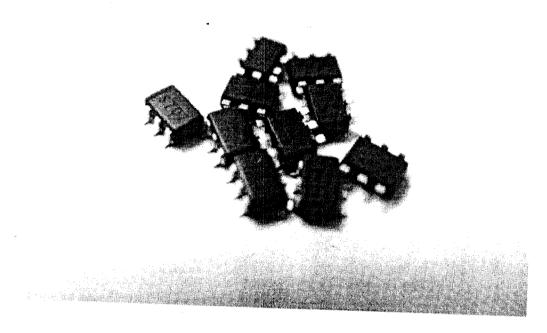


**Test Report** 

No. 2151444/TY

Date: Jun 14 2007

Page 3 of 3



\*\*\*End of Report\*\*\*

This document is issued by the Company subject to its General Conditions of Service printed overleaf or available on request and accessible at <a href="https://www.sgs.com">www.sgs.com</a>. Attention is drawn to the limitations of liability, indemnification and jurisdictional issues defined therein. Unless otherwise stated: (a) the results shown in this document refer only to the sample(s) are retained for 30 days only. This document cannot be reproduced except in full, without prior approval of the Company. Any unauthorized alteration, forgery or falsification of the content or appearance of this report is unlawful and offenders may be prosecuted to the fullest extent of the law.

# R5460 Series

2007/12/27		Package			SO123-6/PLP1820-6	SOT23-6/PI P1820-6	SOT23-6/PLP1820-6	SOT23-6/PLP1820-6	SOT23-6/PLP1820-6	SOT23-6/PLP1820-6	SOT23-6/PLP1820-6			SOT23-6/PLP1820-6	SOT23-6/PLP1820-6	SOT23-6/PLP1820-6	SOT23-6/PLP1820-6	SOT23-6/PLP1820-6	SOT23-6/PLP1820-6		SOT73-6/Pl D1820 6	SOT23-6/PLP1820-6	SOT23-6/PLP1820-6
	٥/ ا	Charge		Ì	ž č	<u> </u>	Q	۵ ک	Šč	58	ð				Š.		1	Ī	$\dashv$		Š		9 S
	1Vdet4		(6)	0	0 . 00	- ∞	ω.	ω .	Σ α	ο ω	8			8	∞ α	ο σ	ν i α	Σ α	ρ N		8	8	8
	tVdet1 tVdet2 tVdet3	(ms)	2011	12	7.2	12	12	12	7 2	12	12			12	7 2	7 (	7.5	7 (	7		12	12	12
	tVdet2	(sm)		128	128	128	128	128	128	128	128			128	128	120	128	α 100 100 100 100 100 100 100 100 100 10	071		128	128	128
	tVdet1	(S)		-	_	_	<del>-</del> -	- ' -										-   -	-		-	-	
	Vdet4	3		-0.400	-0.400	-0.200	-0.200	-0.200	-0.200	-0.200	-0.200			0.400	0 200	-0.200	-0.200	-0.200			-0.200	-0.200	-0.200
	Vdet3	3		0.150	0.200	0.150	0.100	0.200	0.200	0.150	0.200		000	0.200	0.150	0.150	0.200	0.200			0.200	0.200	0.500
	Vrel2L	(X)		3.000	3.000	3.000	3.000	3.000	3.000	3.200	2.500			 		1	1				3.000	2.500	2001
	Vdet2 L	2		2.400	2.300	2.300	2.900	2.300	2.400	3.000	200.0		2 300	2.400	2.300	2.900	2.300	2.800			2.500	2.000	
	Vrei2U	$\mathbb{S}$		3.000	3.000	3.000	3.100	3.000	3.000	3.200 3.200					1	-	1	-			3.000	2.500	
	Vdet2 U	S		2.400	2.300	2.300	2.900	2.300	2.400	3.000			2 300	2.400	2.300	2.900	2.300	2.800			2.500		
	Vrel1L	8		4.050	4.150	4.150	4.050	4.150	4.050	4.050			4.150	4.050	4.150	4.050	4.150	4.050		01.0	3.450	-	
	vaeri O vreii O vaeti L	3		4.250	4.350	4.250	4.290	4.350	4.250	4.290			4.350	4.250	4.350	4.290	4.350	4.250	^	0.00	3.650	3.900	
1 / 2 / 7	vreitu	(X)	4000	4.050	4 150	4.050	4.050	4.150	4.050	4.050			4.150	4.050	4.150	4.050	4.150	4.050	3.65 - 3.90V Tyne>	2 4 50	3.450	3.450	
//4044	O Lan	1.		4.250	4.350	4.250	4.290	4.350	4.250	4.290		ype>	4.350	4.250	4.350	4.230	4.350	4.230	3.65 - 3 9	3 650	3.650	3.900	
	Code	<a auto-release<="" td="" version:=""><td>R5460K/N202AA</td><td>R4560K/N203AA</td><td>R5460K/N204AA</td><td>R5460K/N205AA</td><td>R4560K/N206AA</td><td>R4560K/N20/AA</td><td>R4560K/N211AA</td><td>R4560K/N212AA</td><td></td><td>C version: Latch Type&gt;</td><td>N3400WNZU1AC</td><td>R5460K/N202AC</td><td>R4560K/N206AC</td><td>R4560K/NI207AC</td><td>R4560K/N214AC</td><td>100000000000000000000000000000000000000</td><td><d vdet1="&lt;/td" version:=""><td></td><td>R5460K/N210AD</td><td>R5460K/N213AD</td><td></td></d></td></a>	R5460K/N202AA	R4560K/N203AA	R5460K/N204AA	R5460K/N205AA	R4560K/N206AA	R4560K/N20/AA	R4560K/N211AA	R4560K/N212AA		C version: Latch Type>	N3400WNZU1AC	R5460K/N202AC	R4560K/N206AC	R4560K/NI207AC	R4560K/N214AC	100000000000000000000000000000000000000	<d vdet1="&lt;/td" version:=""><td></td><td>R5460K/N210AD</td><td>R5460K/N213AD</td><td></td></d>		R5460K/N210AD	R5460K/N213AD	



# Li-ION/POLYMER 2-CELL PROTECTOR

# **R5460xxxxxx SERIES**

EA-165-070202

## **OUTLINE**

The R5460xxxxxx Series are high voltage CMOS-based protection ICs for over-charge/discharge of rechargeable two-cell Lithium-ion (Li+) / Lithium polymer, further include a short circuit protection circuit for preventing large external short circuit current and the protection circuits against the excess discharge-current and excess charge current.

Each of these ICs is composed of six voltage detectors, a reference unit, a delay circuit, a short circuit protector, an oscillator, a counter, and a logic circuit. When the over-charge voltage threshold or excess-charge current threshold crosses the each detector threshold from a low value to a high value, the output of Cout pin switches to 控? level after internal fixed delay time. To release over-charge detector after detecting over-charge, the detector can be reset and the output of Cout becomes "H" when a kind of load is connected to VDD after a charger is disconnected from the battery pack and the cell voltage becomes lower than over-charge detector threshold. In case that a charger is continuously connected to the battery pack, if the cell voltage becomes lower than the over-charge detector threshold, over-charge state is also released.

The output of  $D_{OUT}$  pin, the output of the over-discharge detector and the excess discharge-current detector, switches to <table-cell> level after internally fixed delay time, when discharged voltage crosses the detector threshold from a high value to a value lower than  $V_{DET2}$ .

To release over-discharge detector, after detecting over-discharge voltage, connect a charger to the battery pack, and when the battery supply voltage becomes higher than over-discharge detector threshold. In case of "A" version, when the cell voltage becomes equal or more than the released voltage from over-discharge, over-discharge detector is released.

Even if a battery is discharged to 0V, charge current is acceptable.

After detecting excess-discharge current or short current, when the load is disconnected, the excess discharged or short condition is released and Dout becomes 想?

After detecting over-discharge voltage, supply current will be kept extremely low by halting internal circuits' operation.

When the output of Cout is 摁? if V- pin level is set at -1.6V, the delay time of detector can be shortened. Especially, the delay time of the over-charge detector can be reduced into approximately 1/60 and test time for protection circuit PCB can be reduced. The output type of COUT and DOUT is CMOS.

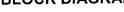
# **FEATURES**

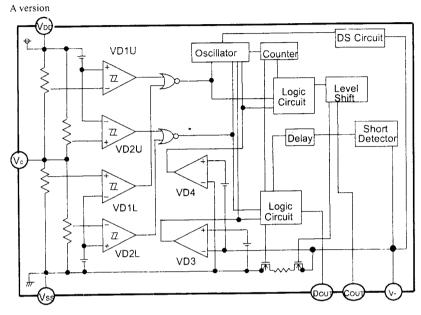
<ul> <li>Manufactured with High Voltage Tolerant Process. Abso</li> <li>Low supply current</li> </ul>		
Low supply current	solute Maximum Rating	
Supp	ply current (At normal mode)	
Stand	IUUV Cliffent	4.0礎
		sion)
High accuracy detector threshold Over-	Max. 0.1μA (B vers	
Over-c Excess	(Topt=-5 to 55癈) ? Om edischarge detector ? .5% ss discharge-current detector	V
Over-discharge detect  Excess dis  3 option	ector threshold $4.1V-4.5V$ step of $0.005V(VD1U/VD1U/VD1U/VD1U/VD1U/VD1U/VD1U/VD1U/$	VD1L) VD2L) 005V •OmV
Over-charge re Over-discharge Internal fixed Output delay time	released voltage 0.1V-0.4V step of 0.05V(VH1U/VH ge released voltage 0.2V-0.7V step of 0.1V(VH2U/VH ge released voltage 0.2V-0.7V step of 0.1V(VH2U/VH ge detector Output Delay 1.0s acharge detector Output Delay 128ms discharge-current detector Output Delay 12r harge-current detector Output Delay 8ms cuit detector Output Delay 300社 is 想?if V- level is set at ? .6V, the Output Delay detector Output Delay 12r detector Output Delay 300社 is 想?if V- level is set at ? .6V, the Output Delay 300社 is detect and release the over-charge an large can be reduced (Delay 1.05)	mV H2L) H3L) ms s
outley charge	, recomes about 1/60 of normal	<i>'</i> 1
Ultra Small package	DI P1000	
APPLICATIONS	101050-6	

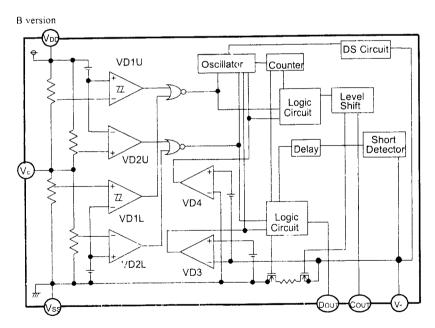
# **APPLICATIONS**

- Li+ / Li Polymer protector of over-charge, over-discharge, excess-current for battery pack
- High precision protectors for cell-phones and any other gadgets using on board Li+ / Li Polymer

# **BLOCK DIAGRAMS**







## **SELECTION GUIDE**

In the R5460xxxxxx Series, input threshold of over-charge, over-discharge, excess discharge current, and the package and taping can be designated.

Part Number is designated as follows:

R5460x  $\underline{xxxxx_x}$ -xx  $\leftarrow$  Part Number  $\uparrow \uparrow \uparrow \uparrow \uparrow$ 

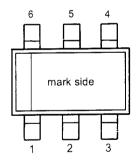
a b cd e

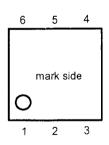
Code	Contents					
а	Package Type N: SOT-23-6 K: PLP1820-6					
ъ	Serial Number for the R5460 Series designating input threshold for over-charge, over-discharge, excess discharge-current detectors.					
С	Designation of Output delay option of over-charge and excess discharge-current.					
d	Designation of version symbols.					
e	Taping Type: TR (refer to Taping Specification)					

# PIN CONFIGURATIONS



PLP1820-6





# **ELECTRICAL CHARACTERISTICS**

Symbol	Item	Conditions	Min.	Typ.	Max.	Un
V <sub>DD</sub> ,	Operating input voltage	Voltage defined as	1	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1		-
		VDD-Vss	1.5	İ	10.0	V
Vst	Minimum operating Voltage for OV charging *Note 1	Voltage defined as VDD-V- VDD-Vss=OV			1.8	V
VDETIU	CFLL1 Over-charge threshold	Detect rising edge of supply voltage R1=330Ω R1=330Ω (Topt=-5 to 55癈) (Note:3	VDET1U-0.025 VDET1U-0.030	VDETIU VDETIU	VDET1U+0.025 VDET1U+0.030	
$V_{\rm CSDD}$	CELL1 Over-charge released voltage	·R1=330Ω	V <sub>RELITI</sub> -0.050	VRELIE	V <sub>PB-3:1+</sub> 0.050	1
:Veen	Output delay of over-charge	VDD=3.5V to 4.5V,Vc-Vss=3.5V	0.7	1.0	1.3	s
'.V <sub>REL1</sub>	Output delay of release from over-charge	VDD=4.5V to 3.5V, $V_C$ - $V_{SS}$ =3.5V	11	16	21	m
Vogru.	CELL2 Over-charge detector threshold	Detect rising edge of supply voltage R1=330 $\Omega$ R1=330 $\Omega$ (Topt=-5 to $55$ 核)*Note3	VDET11-0.025 VDET11-0.030	VDETIL VDETIL	VDET1L+0.025 Viernl+0.030	T,
VRELU	CELL2 Over-charge released voltage	R1=330Ω	VRELIL-0.05	V <sub>RELII</sub>	V. RELIE + 0.05	1
V DET2U	CELL1 Over-discharge threshold	Detect falling edge of supply voltage	Vaetzu×0.975	VDET2U	VDET26×1.025	V
VREL26	CELL1 Released Voltage from Over-discharge	Detect rising edge of supply voltage	Vrelzu×0.975	VREL21	V*81.2 I×1.025	V
VDET2	Output delay of over-discharge	V <sub>DD</sub> -V <sub>C</sub> =3.5V to 2.2V V <sub>C</sub> -V <sub>SS</sub> ≠3.5V	89	128	167	m
VKEL2	Output delay of release from over-discharge	Vpd-Vc=2.2V to 3.5V. Vc-Vss=3.5V	0.7	1.2	1.7	nı
DE12L	CELL2 Over-discharge threshold	Detect falling edge of supply voltage	Vietzu×0.975	VDET2L	Viscoun.<1.025	V
V <sub>KP, fi</sub>	CELL2 Released Voltage from Over-discharge	Detect rising edge of supply voltage	V <sub>dual</sub> x(t,975	VREUZL	V <sub>PEL2D</sub> -1.025	V
VDETO	Excess discharge-current threshold	Detect rising edge of 'V-' pin voltage	Viens-0.015	VDETS	Voca.=0.015	V
VDETS	Output delay of excess discharge cur- rent	VDD-VC=VC-Vss=3.5V, V-=0V to 0.5V	8	12	16	nis
Vesta	Output delay of release from excess discharge-current	$V_{DD-VC}=V_{C}-V_{SS}=3.5V, V-=3V$ to $0V$	0.7	1.2	1.7	ms
VDET4	Excess charge-current threshold	Detect falling edge of 'V-' pin voltage	-0.44 -0.23	-0.40 -0.20	-0.36 -0.17	v
			-0.13	-0.10	-0.07	
VDET4	Output delay of excess charge-current	VDD-VC=VC~Vss=3.5V, V-=0V to -1V	5	8	11	ms
	Output delay of release from excess charge-current	$V_{DD-VC}=V_{C}-V_{SS}=3.5V$ , $V=-1V$ to $0V$	0.7	1.2	1.7	m
short	Short protection voitage	VDD.VC=VC-VSS=3.5V	0.6	1.0	1.4	v
short		VDD-VC=Vc-Vss=3.5V, V=0V to 2V	230	300	500	衽
Rshort		V <sub>DD</sub> =7.2V, V-=1V	25	40	75	kΩ
/ps	Delay Shortening Mode input voltage	VDD-V-3-V <sub>0</sub> -V <sub>88</sub> =4,4V	-2.2	-1.6	-1.0	ν
Joli	Nch ON voltage of Cort	Iol=50		0.4	0.5	V
Joi:1	Pch ON voltage of Coco	Ioh=-50礎 VDD-Vc=Vc-Vss=3.9V	6.8	7.4		V
тора	Nch ON voltage of Dour	Io=50礎 VDD-Vc=Vc-Vss=2.0V		0.2	0.5	V
7он2	Pch ON voltage of Dout	Ioh=-50@	6.8	77.4		V
מנ	Supply current	V <sub>DD-</sub> V <sub>C-</sub> -V <sub>C-</sub> V <sub>SS</sub> =3.9V	-	4.0	8.0	礎
	Standby current	V <sub>DD</sub> -V <sub>C</sub> =V <sub>C</sub> -V <sub>SS</sub> =2V		1.2	U.U.	HAT.

# PIN DESCRIPTION

Pin No.							
SOT23-6	PLP1820-6	Symbol	Description				
11	3	Dout	Output pip of array 1				
2	1	Соит	Output pin of over-discharge detection, CMOS output				
3	2	COUT	Output pin of over-charge detection, CMOS output				
	2	V-	Pin for charger negative input				
4	6	VC					
5	5	* * * 7	Input Pin of the center voltage between two-cell				
		• V <sub>DD</sub>	Power supply pin, the substrate voltage level of the IC.				
6	4	Vss	Vss pin. Ground pin for the IC				

# ABSOLUTE MAXIMUM RATINGS

Symbol	ltem	Dotin	
V <sub>DD</sub>	Supply voltage	Ratings	Uni
	Input Voltage	-0.3 to 12	V
Vc V-	Center pin voltage between two-cell	Vss -0.3 to V <sub>DD</sub> +0.3	V
	Charger negative input V- pin Output voltage	V <sub>DD</sub> -30 to V <sub>DD</sub> +0.3	_
VCout	Cout pin	V <sub>DD</sub> -30 to V <sub>DD</sub> +0.3	
VDout	Dout pin	Vss -0.3 to V <sub>DD</sub> +0.3	V
PD	Power dissipation	150	
Topt	Operating temperature range	-40 to 85	mW
Tstg	Storage temperature range	-55 to 125	粉

Symbol	Item	Conditions	Min.	Тур.	ied, Topt=2	Ur
VDD1	Operating input voltage	Voltage defined as		Typ.		-0
		VDD-Vss	1.50		10.0	1
Vst	Minimum operating Voltage for	, , ,			<u> </u>	+
	OV charging *Note 1	V <sub>DD</sub> -V <sub>SS</sub> =0V		ĺ	1.8	V
VDET1U	CELL1 Over-charge threshold	Detect rising edge of supply voltage			<del>                                     </del>	+
	obbbi over-charge threshold	R1=330Ω R1=330Ω (Topt=-5 to 55癈) Note3	VDET1U-0.025		1.00.000	
VRELIU	CELL1 Over-charge released voltage	R1=330Ω	VRELIU-0.030	V <sub>DET1U</sub>	VDET1U+0.030	
tV <sub>DET1</sub>	Output delay of over-charge	VDD=3.5V to 4.5V,Vc-Vss=3.5V	0.7	1.0	V <sub>RELIG</sub> +0.05	
tV <sub>REL1</sub>	Output delay of release from over-charge	VDD=4.5V to 3.5V, V <sub>C</sub> -V <sub>SS</sub> =3.5V	111	16	21	S
	CPV 2 C	Detect rising edge of supply voltage		10	21	m
VDETIL	CELL2 Over-charge detector threshold	R1=330Ω	VDET11-0.025	VDETIL	VDETIL+0.025	1
VRELIL	CELL2 Over-charge released voltage	R1=330Ω (Topt=-5 to 55癈) *Note3	VDET 01-0.030	VDETIL	VDETIL+0.030	V
	CELL1 Over-discharge threshold	R1=330Ω	V <sub>RELIL</sub> -0.050	VRELIL	VRELIE+0.050	
VDET2		Detect falling edge of supply voltage  Vpp-Vc=3.5V to 2.2V	VDET2U×0.975	VDET2U	Vug:20×1.025	V
V DET2	Output delay of over-discharge	V <sub>D</sub> -V <sub>C</sub> =3.5V to 2.2V V <sub>C</sub> -V <sub>S</sub> =3.5V	89	128	167	m
VREL2	Output delay of release from over-discharge	Vpp-Vc=2.2V to 3.5V	0.7	1.0	t	-
DET2L		V <sub>C</sub> -V <sub>SS</sub> =3.5V	0.7	1.2	1.7	m
VDETS I	CELL2 Over-discharge threshold  Excess discharge-current threshold	Detect falling edge of supply voltage	VDET24×0.975	V <sub>DET2</sub> L	Vietal×1.025	V
1	Output delay of excess discharge	Detect rising edge of 'V-' pin voltage	VDETS-0 015	VDETS	Voi;::: +0.015	V
VDET3	current	V <sub>DD</sub> -V <sub>C</sub> =V <sub>C</sub> -V <sub>SS</sub> =3.5V, V-=0V to 0.5V	8	12	16	m
/REL3	Output delay of release from	VDD-VC=VC-Vss=3.5V, V-=3V	<del> </del>			1
RELS	excess discharge-current	to 0V	0.7	1.2	1.7	ms
		Detect falling edge of 'V-' pin voltage	-0.44	-0.40	-0.36	ļ ———
DET4 E			-0.23	-0.20	-0.17	v
			-0.13	-0.10	-0.17	V
DET4 C	Output delay of excess charge-current	V <sub>DD-</sub> V <sub>C</sub> =V <sub>C</sub> -V <sub>SS</sub> =3.5V, V-=0V to				-
		-1 V	5	8	11	ms
REL4	Output delay of release from excess harge-current	VDD-VC=VC-VSS=3.5V, V-=-1V	0.7	1.2	1.7	
	Short protection voltage	to 0V		1.2	1.7	ms
		V <sub>DD-</sub> V <sub>C</sub> =V <sub>C</sub> -V <sub>SS</sub> =3.5V	0.6	1.0	1.4	V
hort C	Output Delay of Short protection	V <sub>DD-</sub> V <sub>C</sub> =V <sub>C</sub> -V <sub>SS</sub> =3.5V, V-=0V to 2V	230	300	500	żΞ
short ]	Reset resistance for Excess					
	discharge-current protection	V <sub>DD</sub> =7.2V, V <sub>-=1</sub> V	25	40	75	$k\Omega$
DS I	Delay Shortening Mode input	VDD-VC=V <sub>C</sub> -V <sub>SS</sub> =4.4V				
			-2.2	-1.6	-1.0	V
ori [	TOTAL VOILAGE OF COURT	Iol=50礎		0.4	0.5	V
	1	VDD-Vc=Vc-Vss=4.5V loh=-50(標		0.4	0.5	V
онт Н	CH ON VOILAGE OF COURT		68	7.4	-	V
DL2 N		Iol=50礎				
71.2	TOLL OIL VOLLAGE OF DOUT	VDD-Vc=Vc-Vss=2.0V		0.2	0.5	V
oH2 F	Pch ON voltage of Doug	Ioh=-50健,		+		
	on on voltage of Boot	VDD-Vc=Vc-Vss=3.9V	6.8	7.4		V
	supply current	V <sub>DD</sub> -V <sub>C</sub> =V <sub>C</sub> -V <sub>SS</sub> =3.9V		4.0	8.0	礎
IS		V <sub>DD</sub> -V <sub>C</sub> =V <sub>C</sub> -V <sub>SS</sub> =2V				碰

#### **OPERATION**

#### • VDET1U, VDET1L / Over-Charge Detectors

The VDET1U and VDET1L monitor the voltage between  $V_{DD}$  pin and  $V_{C}$  pin (the voltage of Cell1) and the voltage between  $V_{C}$  pin and  $V_{SS}$  pin (the voltage of Cell2), if either voltage becomes equal or more than the over-charge detector threshold, the over-charge is detected, and an external charge control Nch MOSFET turns off with Cout pin being at "L" level.

VDET1U is the detector of Cell1, and the VDET1L is the detector of Cell2.

To reset the over-charge and make the Cout pin level to "H" again after detecting over-charge, in such conditions that a time when the both Cell1 and Cell2 are down to a level lower than over-charge voltage, by connecting a kind of load to Vdd after disconnecting a charger from the battery pack. Then, the output voltage of Cout pin becomes "H", and it makes an external Nch MOSFET turn on, and charge cycle is available. In other words, once over-charge is detected, even if the supply voltage becomes low enough, if a charger is continuously connected to the battery pack, recharge is not possible. Therefore this over-charge detector has no hysteresis. To judge whether or not load is connected, the built-in excess-discharge current detector is used. By connecting some load, V- pin voltage becomes equal or more than excess-discharge current detector threshold, and reset the over-charge detecting state.

Further, either or both voltage of Cell1 and Cell2 is higher than the over-charge detector threshold, if a charger is removed and some load is connected, COUT outputs 拱? however, load current can flow through the parasitic diode of the external charge control Nch MOSFET. After that, when the VDD pin voltage becomes lower than the over-charge detector threshold, COUT becomes 提?

Internal fixed output delay times for over-charge detection and release from over-charge exist. If either or both of the voltage of Cell1 or Cell2 keeps its level more than the over-charge detector threshold, and output delay time passes, over-charge voltage is detected. Even when the voltage of Cell1 or Cell2 pin level becomes equal or higher level than VDETT if these voltages would be back to a level lower than the over-charge detector threshold within a time period of the output delay time, the over-charge is not detected. Besides, after detecting over-charge, while the both of Cell1 and Cell2 voltages are lower than the over-charge detector threshold, even if a charger is removed and a load is connected, if the voltage is recovered within output delay time of release from over-charge, over-charge state is not released.

A level shifter incorporated in a buffer driver for the Cout pin makes the "L" level of Cout pin to the V - pin voltage and the "H" level of Cout pin is set to VDD voltage with CMOS buffer.

## • VDET2U, VDET2L / Over-Discharge Detectors

The VDET2U and VDET2L monitor the voltage between VDD pin and VC pin (Cell1 voltage) and the voltage between VC pin and VSS pin (Cell2 Voltage). When either of the cell1 or cell2 voltage becomes equal or less than the over-discharge detector threshold, the over-discharge is detected and discharge stops by the external discharge control Nch MOSFET turning off with the Dout pin being at "L" level.

The reset resistor of excess discharge-current is off at normal state. Only when detecting excess discharge-current or short circuit, the resistor is on.

Output delay time of excess discharge-current is set shorter than the delay time for over-discharge detector. Therefore, if VDD voltage would be lower than VDET2 at the same time as the excess discharge-current is detected, the R5460xxxxxx is at excess discharge-current detection mode. By disconnecting a load, VDET3 is automatically released from excess discharge-current.

#### • VDET4/ Excess charge-current detector

When the battery pack is chargeable and discharge is also possible, VDET4 senses V- pin voltage. For example, in case that a battery pack is charged by an inappropriate charger, an excess current flows, then the voltage of V- pin becomes equal or less than excess charge-current detector threshold. Then, the output of Cout becomes "L", and prevents from flowing excess current in the circuit by turning off the external Nch MOSFET.

Output delay of excess charge current is internally fixed. Even the voltage level of V- pin becomes equal or lower than the excess charge-current detector threshold, the voltage is higher than the VDET4 threshold within the delay time, the excess charge current is not detected. Output delay for the release from excess charge current is also set.

VDET4 can be released with disconnecting a charger and connecting a load.

#### . DS (Delay Shorten) function

Output delay time of over-charge, over-discharge, and release from those detecting modes can be shorter than those setting value by forcing equal or less than the delay shortening mode voltage to V-pin when the COUT is 想?

#### Operation against 2-Cell Unbalance

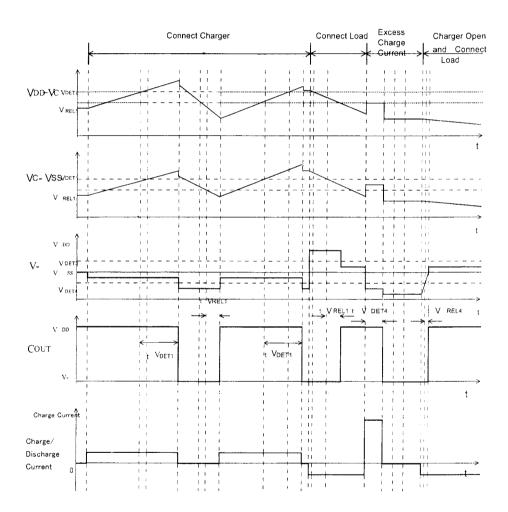
A version: If one of the cells detects over-charge and the output of COUT becomes "L" and keeps the status, even if the other cell detects over-charge or over-discharge or short, the over-charge status is maintained and the output of COUT keeps "L". If one of the cell detects over-charge and the output of COUT becomes "L", the other cell detects over-discharge and the former cell is released from over-charge, after the delay time of the released from over-charge, the output of COUT becomes "H", and after the delay time of detecting over-discharge, the output of DOUT becomes "L". After detecting over-discharge, A version halts internal unnecessary circuits and be into the standby mode. (Supply current Max. 2.0µA)

B version: If one of the cells detects over-charge and the output of Cout becomes "L" and keeps the status, even if the other cell detects over-charge or over-discharge or short, the over-charge status is maintained and the output of Cout keeps "L". If one of the cells detects over-discharge and the output of Dout becomes "L", even if the other cell detects over-charge, the former cell also detects over-discharge, therefore, the output of Dout keeps "L". After detecting over-discharge, B version halts internal unnecessary circuits and becomes into the standby mode. (Supply current Max. 0.1µA).

Both A version and B version, the external FETs do not turn off at the same time.

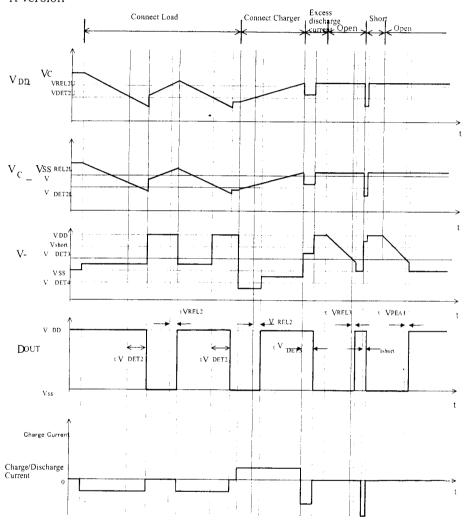
# **TIMING CHART**

(1) Timing diagram of Over-charge, Excess charge current

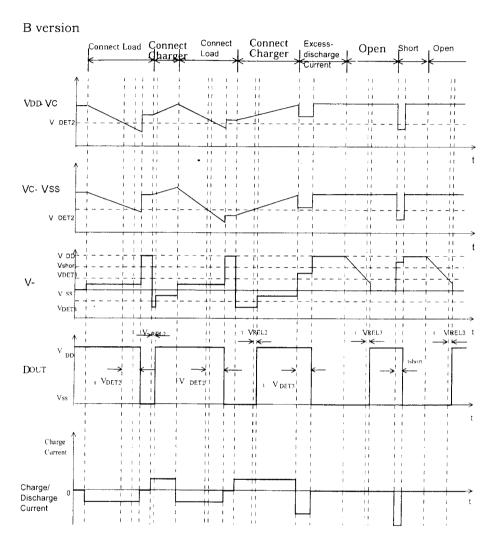


# (2) Over-discharge, Excess discharge current, Short circuit

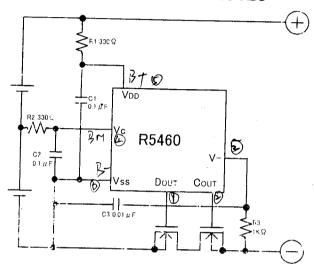
## A version







# TYPICAL APPLICATION AND TECHNICAL NOTES



## **TECHNICAL NOTES**

R1, R2, C1 and C2 stabilize a supply voltage to the R5460xxxxxx. A recommended R1, R2 value is less than  $1k\Omega$ .

A larger value of R1 and R2 makes the detection voltage shift higher because of some conduction current in the R5460xxxxxx.

To stabilize the operation, the value of C1 and C2 should be equal or more than  $0.01 \mu \text{F}.$ 

R1 and R3 can operate also as parts for current limit circuit against reverse charge or applying a charger with excess charging voltage beyond the absolute maximum rating of the R5460xxxxxx, the battery pack. Small value of R1 and R3 may cause over-power consumption rating of power dissipation of the R5460xxxxx. Thus, the total value of 'R1+R3' should be equal or more than  $1k\Omega$ .

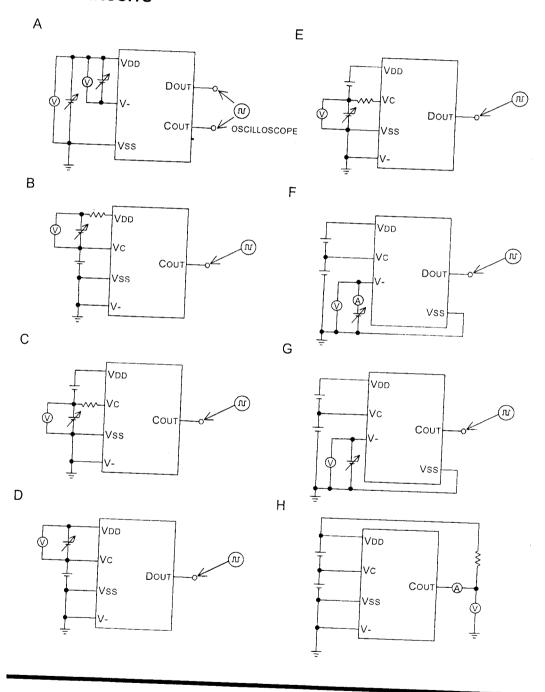
If R3 value is set too large, after detecting over-discharge, release operation by connecting a charger may be impossible, our recommendation value as R3 is  $3k\Omega$  or less.

To stabilize the operation of the IC, use 0.01µF or more capacitor as C3.

The typical application circuit diagram is just an example. This circuit performance largely depends on the PCB layout and external components. In the actual application, fully evaluation is necessary. Over-voltage and the over current beyond the absolute maximum rating should not be forced to the protection IC and external components.

Ricoh cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Ricoh product. If technical notes are not complied with the circuit which is used Ricoh product, Ricoh is not responsible for any damages and any accidents.

# **TEST CIRCUITS**



İ Voo Соит Vc Vss J Vdd Vc DOUT Vss Κ VDD DOUT Vc Vss L VDD VC

R5460xxxxxx

Typical Characteristics were obtained with using those above circuits:

Vss

Test Circuit A: Part1: Typical characteristics 1)

Test Circuit B: Part1: Typical characteristics 2) 4) 6) 7)

Test Circuit C: Part1: Typical characteristics 3) 5)

Test Circuit D: Part1: Typical characteristics 8) 10) 12) 13)

Test Circuit E: Part1: Typical characteristics 9) 11)

Test Circuit F: Part1: Typical characteristics 14) 15) 16) 17) 18) 19)

Test Circuit G: Part1: Typical characteristics 20) 21) 22) 23)

Test Circuit H: Part1: Typical characteristics 24)

Test Circuit I: Part1: Typical characteristics 25)

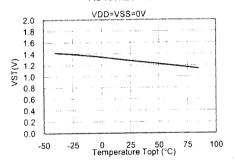
Test Circuit J: Part1: Typical characteristics 26)

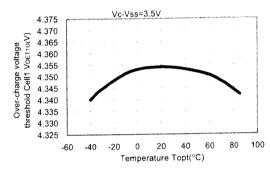
Test Circuit K: Part1: Typical characteristics 27)

Test Circuit L: Part1: Typical characteristics 28) 29) 30)

# **TYPICAL CHARACTERISTICS (Part 1)**

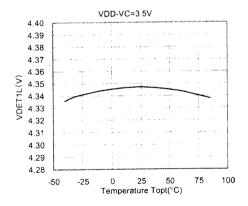
1) Minimum Operating Voltage for 0V Cell Charging 2) Over-charge voltage threshold (Cell1) vs. Temperature R5460x201AB R5460x201AB



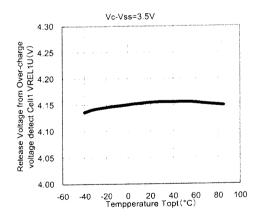


- 3) Over-Charge Voltage Threshold (Cell2) vs. Temperature
- 4)Release Voltage from Over-charge (Cell1) vs. Temperature

#### R5460x201AB



#### R5460x201AB



To reset the over-discharge detector, if both voltages of Cell1 and Cell2 are equal or lower than the over-discharge detector threshold, a charge current flows through the parasitic diode of the external MOSFET. Then, when the VDD voltage becomes higher than the over-discharge detector threshold, Dout becomes ##? and the external MOSFET turns on and discharge will be possible. After connecting a charger, if both voltages of cell1 and cell2 are higher than over-discharge detector threshold, Dout becomes "H" immediately. In the case of A version, even if a charger is not connected, when the Cell1 and Cell2 voltages become equal or more than the released voltage from over-discharge, the over-discharge is released and the voltage of the Dout pin becomes ##? Therefore, the over-discharge detector of A version has some hysterisis.

When a cell voltage equals to zero, if the voltage of a charger is equal or more than OV-charge minimum voltage (Vst), Cout pin becomes "H" and a system is allowable to charge.

The output delay time for over-discharge detect is fixed internally. Even if the voltage of Cell1 or Cell2 is down to equal or lower than the over-discharge detector threshold, if the voltage of Cell1 or Cell2 would be back to a level higher than the over-discharge detector threshold within a time period of the output delay time, the over-discharge is not detected. Output delay time for release from over-discharge is also set.

After detecting over-discharge, supply current would be reduced and be into standby by halting unnecessary circuits and consumption current of the IC itself is made as small as possible.

The output type of Dout pin is CMOS having "H" level of VDD and "L" level of Vss.

# VDET3 /Excess discharge-current Detector, Short Circuit Protector

Both of the excess current detector and short circuit protection can work when the both of control FETs are in "ON" state.

When the V- pin voltage is up to a value between the short protection voltage Vshort /VDD and excess discharge-current threshold VDET3, VDET3 operates and further soaring of V- pin voltage higher than Vshort makes the short circuit protector enabled. This leads the external discharge control Nch MOSFET turns off with the Dout pin being at "L" level.

An output delay time for the excess discharge-current detector is internally fixed.

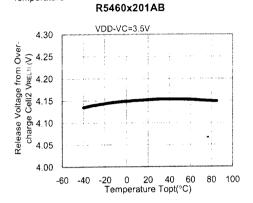
A quick recovery of V- pin level from a value between Vshort and VDET3 within the delay time keeps the discharge control FET staying "H" state. Output delay time for Release from excess discharge-current detection is also set.

When the short circuit protector is enabled, the Dour would be "L" and the delay time is also set.

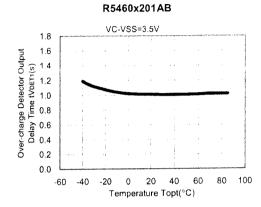
The V - pin has a built-in pull-down resistor to the Vss pin, that is, the resistance to release from excess-discharge current.

After an excess discharge-current or short circuit protection is detected, removing a cause of excess discharge-current or external short circuit makes an external discharge control FET to an "ON" state automatically with the V- pin level being down to the Vss level through the built-in pulled down resistor.

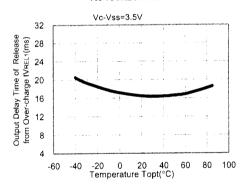
 Release Voltage from Over-charge (Cell2) vs. Temperature



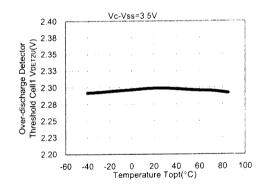
6) Output Delay of Over-charge Detector vs. Temperature



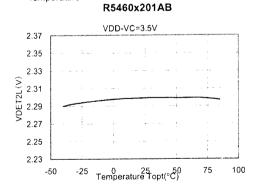
7) Output Delay of Release from Over-charge vs. Temperature R5460x201AB



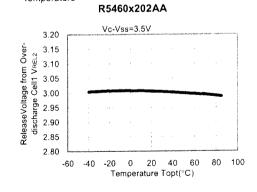
8) Over-discharge Detector Threshold (Cell1) vs. Temperature R5460x201AB



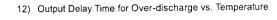
 Over-discharge Detector Threshold (Cell2) vs. Temperature

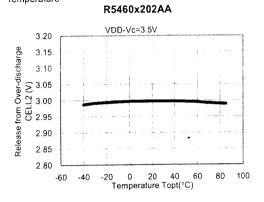


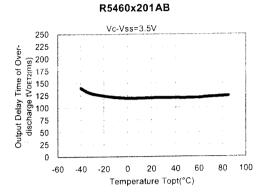
10) Release Voltage from Over-discharge (Cell1) vs. Temperature



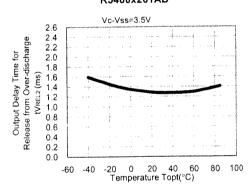
11) Release Voltage from Over-discharge (Cell2) vs. Temperature



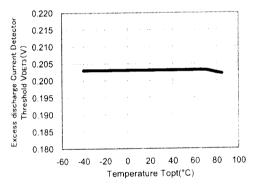




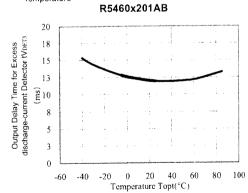
R5460x201AB



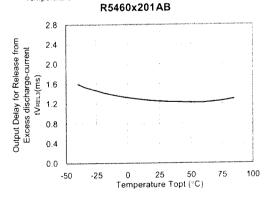
13) Output Delay of Release from Over-discharge vs. Temperature 14) Excess discharge Current Detector Threshold vs. Temperature R5460x201AB



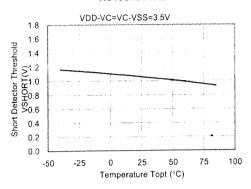
15) Output Delay Time for Excess discharge-current Detector vs. Temperature

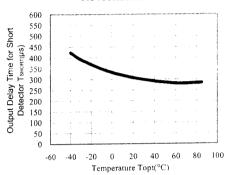


Output Delay for Release from Excess discharge-current vs. 16)



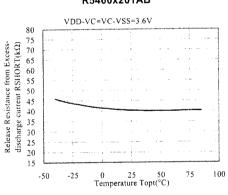
17) Short Detector Voltage Threshold vs. Temperature 18) Output Delay for Short Detector vs. Temperature R5460x201AB R5460x201AB



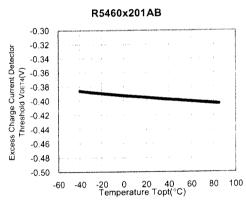


19) Release resistance from Excess-discharge current vs. Temperature

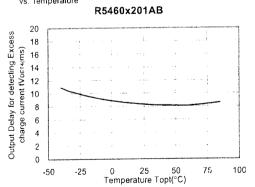
R5460x201AB

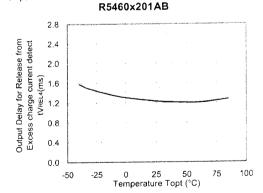


20) Excess-charge current Detector Threshold vs. Temperature

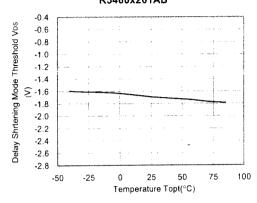


21) Output Delay Time of Excess-charge current Detector Threshold 22) Output Delay Time for Release from Excess-charge current vs. vs. Temperature

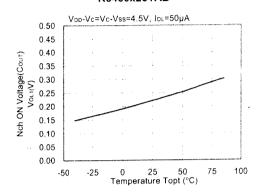




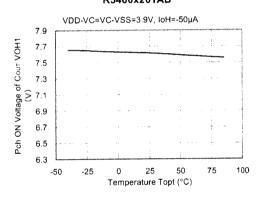
# 23) Delay Shortening Mode Voltage vs. Temperature R5460x201AB



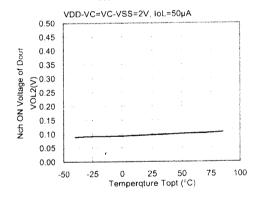
# 24) Nch ON Voltage of Cout vs. Temperature R5460x201AB



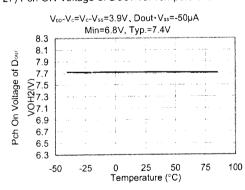
25) Pch ON Voltage of Cout vs. Temperature R5460x201AB



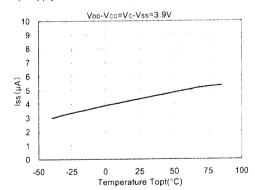
26) Nch ON Voltage of Dout vs. Temperature R5460x201AB



27) Pch ON Voltage of Dout vs. Temperature

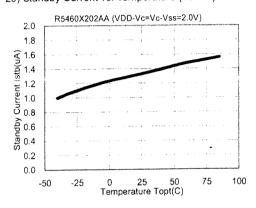


28) Supply Current vs. Temperature

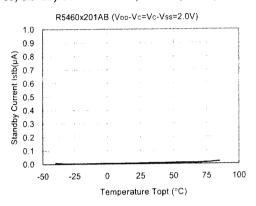




## 29) Standby Current vs. Temperature (Ver. A.)

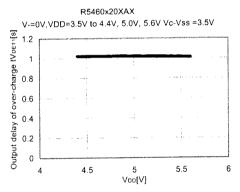


30) Standby Current vs. Temperature (Ver. B.)

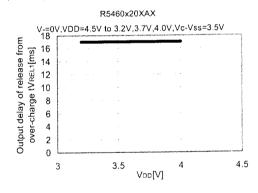


Part 2 Delay Time dependence on  $V_{\text{DD}}$ 

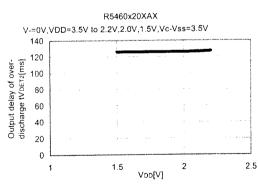
1) Delay Time for Over-charge detector vs. Voo



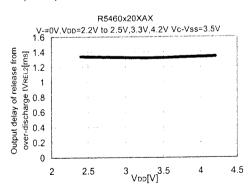
2) Delay Time for Release from Over-charge vs. VDD



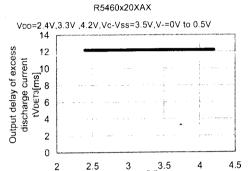
3) Output Delay of Over-discharge detector vs.  $V_{\text{DD}}$ 



4) Output Delay for Release from Over-discharge vs. VDD

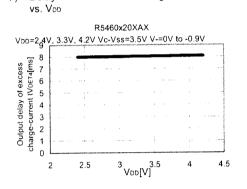


5) Output Delay for Excess Discharge Current vs. V<sub>DD</sub>

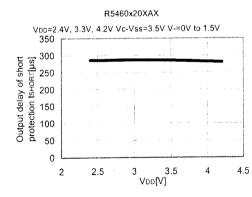


2 2.5 3 3.5 4 4.5 VDD[V]

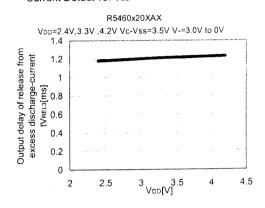
7) Delay Time for Excess Charge Current Detector



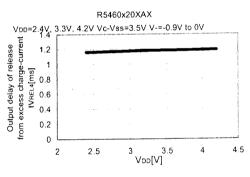
9) Output Delay for Short vs. Voo



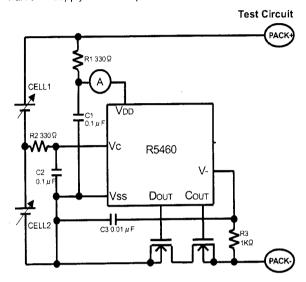
6) Output Delay for Release from Excess Discharge Current Detect vs. Vpp



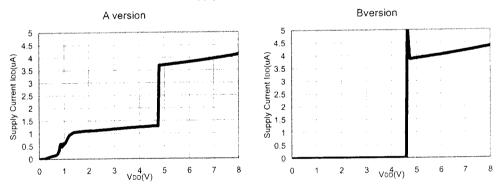
8) Delay Time for release from Excess charge current detect vs. Vop

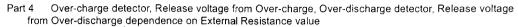


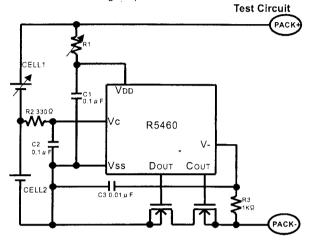
Part 3 Supply Current dependence on Voo



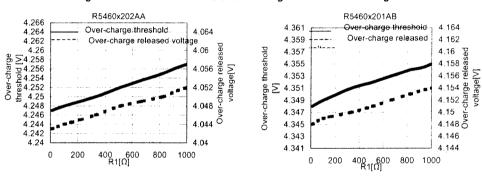
## Supply Current vs. VDD



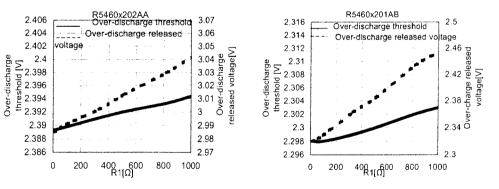




## Over-charge Detector Threshold / Released Voltage from Over-discharge vs. R1

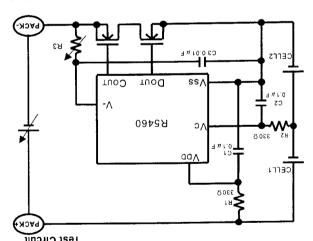


#### Over-discharge / Released from Over-charge Threshold vs. R1



Part 5 Charger Voltage at Released from Over-discharge with a Charger dependence on R2

Test Circuit



Charger Voltage at Release from Over-discharge with a charger vs.  $\ensuremath{\mathsf{R}}\xspace \ensuremath{\mathsf{Z}}\xspace$ 

